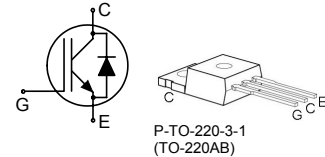


Low Loss DuoPack : IGBT in Trench and Fieldstop technology
with soft, fast recovery anti-parallel EmCon HE diode

- Short circuit withstand time – 10 μ s
- Designed for :
 - Soft Switching Applications
 - Induction Heating
- Trench and Fieldstop technology for 1200 V applications offers :
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - easy parallel switching capability due to positive temperature coefficient in $V_{CE(sat)}$
 - Very low $V_{ce(sat)}$
- Very soft, fast recovery anti-parallel EmCon™ HE diode
- Low EMI
- Application specific optimisation of inverse diode



Type	V_{CE}	I_C	$V_{CE(sat), T_J=25^\circ C}$	$T_{j,max}$	Marking	Package	Ordering Code
IHW10T120	1200V	10A	1.7V	150°C	H10T120	TO-220-3-1	Q67040-S4650

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
DC collector current	I_C		A
$T_C = 25^\circ C$		16	
$T_C = 100^\circ C$		10	
Pulsed collector current, t_p limited by $T_{j,max}$	I_{Cpuls}	24	
Turn off safe operating area $V_{CE} \leq 1200V, T_J \leq 150^\circ C$	-	24	
Diode forward current	I_F		
$T_C = 25^\circ C$		11	
$T_C = 100^\circ C$		7	
Diode pulsed current, t_p limited by $T_{j,max}, T_C = 25^\circ C$	I_{Fpuls}	16.5	
Diode surge non repetitive current, t_p limited by $T_{j,max}$	I_{FSM}		A
$T_C = 25^\circ C, t_p = 10ms$, sine halfwave		28	
$T_C = 25^\circ C, t_p \leq 2.5\mu s$, sine halfwave		50	
$T_C = 100^\circ C, t_p \leq 2.5\mu s$, sine halfwave		40	
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time ¹⁾ $V_{GE} = 15V, V_{CC} \leq 1200V, T_J \leq 150^\circ C$	t_{SC}	10	μs
Power dissipation, $T_C = 25^\circ C$	P_{tot}	138	W
Operating junction temperature	T_J	-40...+150	$^\circ C$
Storage temperature	T_{stg}	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

¹⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.9	K/W
Diode thermal resistance, junction – case	R_{thJCD}		2.6	
IGBT thermal resistance, junction – ambient	R_{thJA}		62	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.5mA$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=10A$ $T_j=25^\circ\text{C}$ $T_j=125^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	1.7	2.2	
			-	2.0	-	
			-	2.2	-	
Diode forward voltage	V_F	$V_{GE}=0V, I_F=4A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	1.65	2.15	
			-	1.7	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=0.6mA, V_{CE}=V_{GE}$	5.0	5.8	6.5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1200V,$ $V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	-	0.2	mA
			-	-	2.0	
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=10A$	-	10	-	S
Integrated gate resistor	R_{Gint}		none			Ω

Dynamic Characteristic

Input capacitance	C_{iss}	$V_{CE}=25V,$	-	606	-	pF
Output capacitance	C_{oss}	$V_{GE}=0V,$	-	48	-	
Reverse transfer capacitance	C_{riss}	$f=1MHz$	-	29	-	
Gate charge	Q_{Gate}	$V_{CC}=960V, I_C=10A$ $V_{GE}=15V$	-	53	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	-	13	nH
Short circuit collector current ¹⁾	$I_{C(SC)}$	$V_{GE}=15V, t_{SC} \leq 10\mu s$ $V_{CC}=600V,$ $T_j=25^\circ C$	-	48	-	A

Switching Characteristic, Inductive Load, at $T_j=25^\circ C$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

IGBT Characteristic

Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ C,$ $V_{CC}=610V, I_C=10A,$ $V_{GE}=0/15V,$ $R_G=81\Omega,$ $L_{\sigma}^{2)}=180nH,$ $C_{\sigma}^{2)}=39pF$ Energy losses include "tail" and diode reverse recovery.	-	45	-	ns
Rise time	t_r		-	20	-	
Turn-off delay time	$t_{d(off)}$		-	520	-	
Fall time	t_f		-	82	-	
Turn-on energy	E_{on}		-	0.68	-	mJ
Turn-off energy	E_{off}		-	0.78	-	
Total switching energy	E_{ts}		-	1.46	-	

Anti-Parallel Diode Characteristic

Diode reverse recovery time	t_{rr}	$T_j=25^\circ C,$	-	115	-	ns
Diode reverse recovery charge	Q_{rr}	$V_R=800V, I_F=4A,$	-	330	-	nC
Diode peak reverse recovery current	I_{rrm}	$di_F/dt=750A/\mu s$	-	7.15	-	A

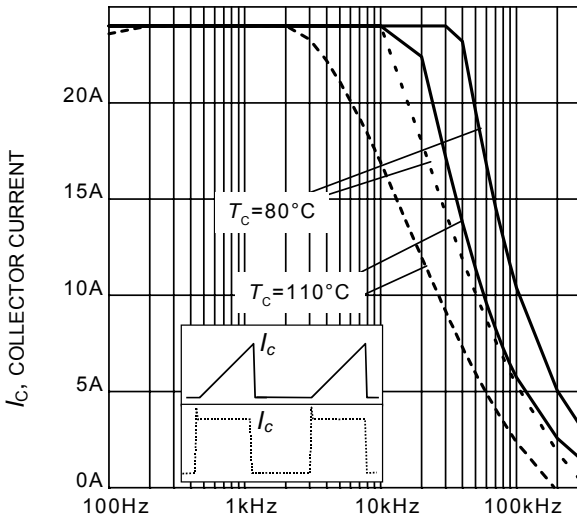
¹⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

²⁾ Leakage inductance L_{σ} and Stray capacity C_{σ} due to dynamic test circuit in Figure E.

Switching Characteristic, Inductive Load, at $T_j=150^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$, $V_{CC}=610\text{V}$, $I_C=10\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=81\Omega$ $L_\sigma^{1)}=180\text{nH}$, $C_\sigma^{1)}=39\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	45	-	ns
Rise time	t_r		-	24	-	
Turn-off delay time	$t_{d(off)}$		-	592	-	
Fall time	t_f		-	177	-	
Turn-on energy	E_{on}		-	0.83	-	mJ
Turn-off energy	E_{off}		-	1.19	-	
Total switching energy	E_{ts}		-	2.02	-	
Anti-Parallel Diode Characteristic						
Diode reverse recovery time	t_{rr}	$T_j=150^\circ\text{C}$	-	185	-	ns
Diode reverse recovery charge	Q_{rr}	$V_R=800\text{V}$, $I_F=4\text{A}$,	-	630	-	nC
Diode peak reverse recovery current	I_{rrm}	$di_F/dt=750\text{A}/\mu\text{s}$	-	8.1	-	A

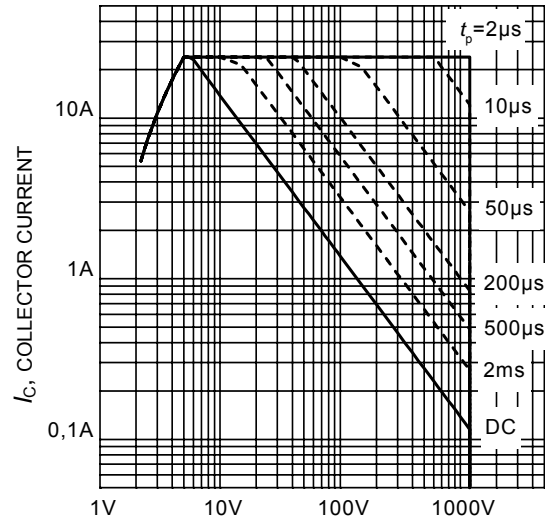
¹⁾ Leakage inductance L_σ and Stray capacity C_σ due to dynamic test circuit in Figure E.



f , SWITCHING FREQUENCY

Figure 1. Collector current as a function of switching frequency

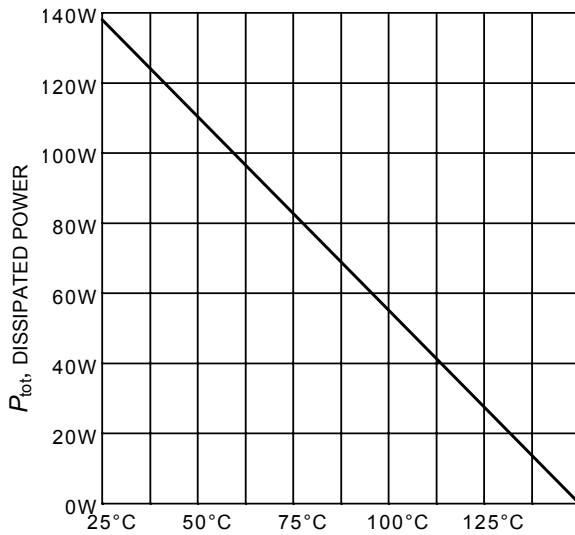
($T_j \leq 150^\circ\text{C}$, $D = 0.5$, $V_{CE} = 600\text{V}$,
 $V_{GE} = 0/+15\text{V}$, $R_G = 81\Omega$)



V_{CE} , COLLECTOR-EMITTER VOLTAGE

Figure 2. Safe operating area

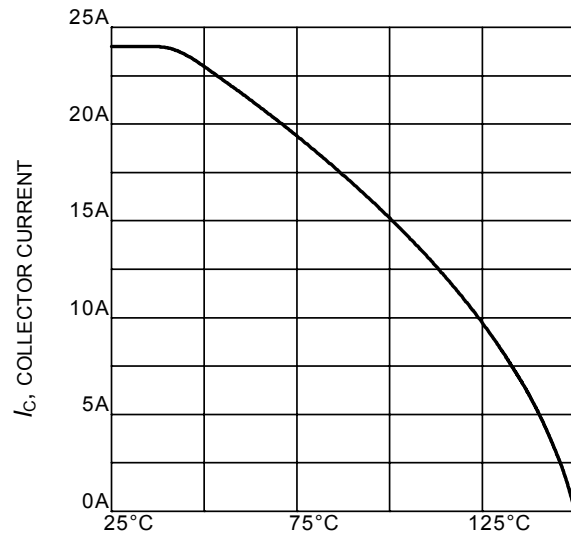
($D = 0$, $T_C = 25^\circ\text{C}$,
 $T_j \leq 150^\circ\text{C}$; $V_{GE} = 15\text{V}$)



T_C , CASE TEMPERATURE

Figure 3. Power dissipation as a function of case temperature

($T_j \leq 150^\circ\text{C}$)



T_C , CASE TEMPERATURE

Figure 4. Collector current as a function of case temperature

($V_{GE} \geq 15\text{V}$, $T_j \leq 150^\circ\text{C}$)

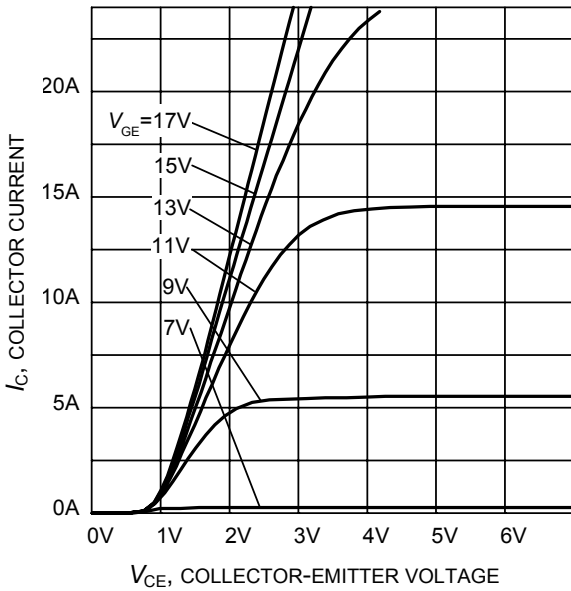


Figure 5. Typical output characteristic
($T_j = 25^\circ\text{C}$)

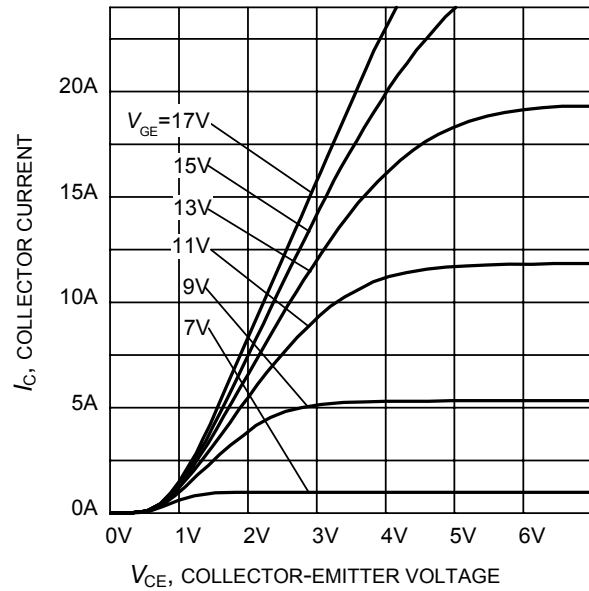


Figure 6. Typical output characteristic
($T_j = 150^\circ\text{C}$)

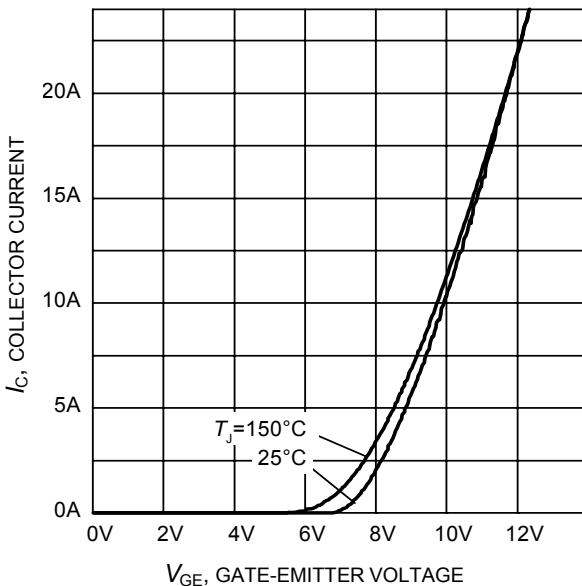


Figure 7. Typical transfer characteristic
($V_{CE} = 20\text{V}$)

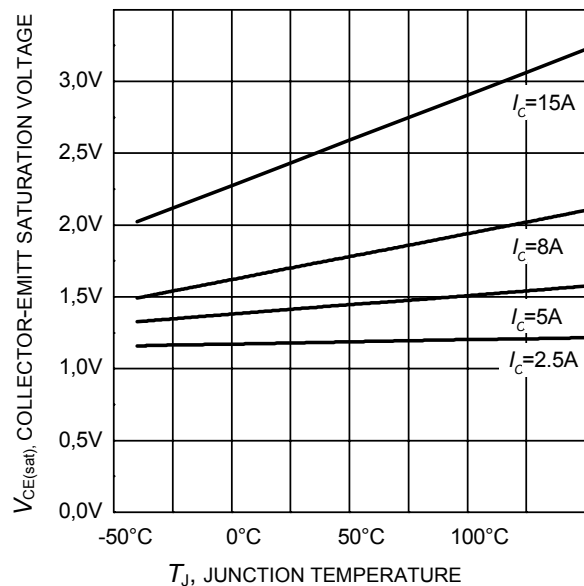


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

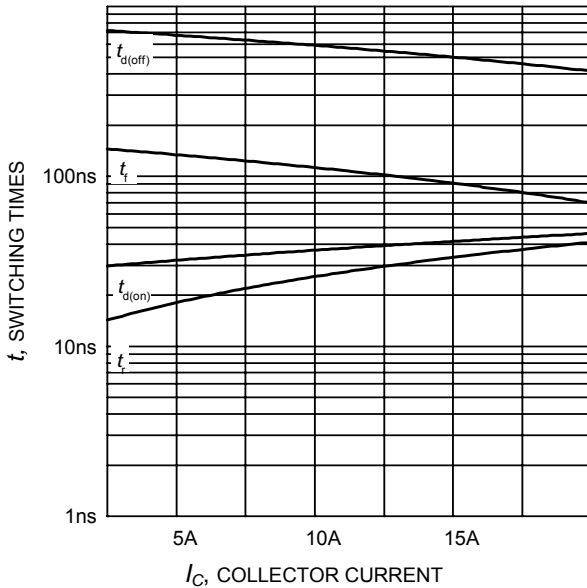


Figure 9. Typical switching times as a function of collector current
 (inductive load, $T_J=150^{\circ}\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=81\Omega$,
 Dynamic test circuit in Figure E)

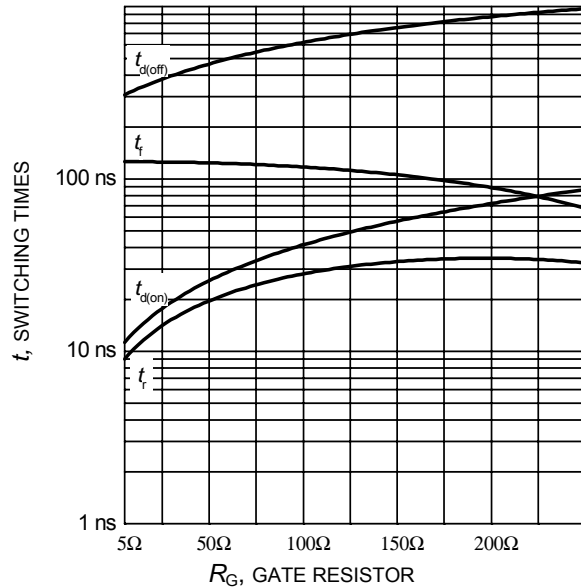


Figure 10. Typical switching times as a function of gate resistor
 (inductive load, $T_J=150^{\circ}\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=8\text{A}$,
 Dynamic test circuit in Figure E)

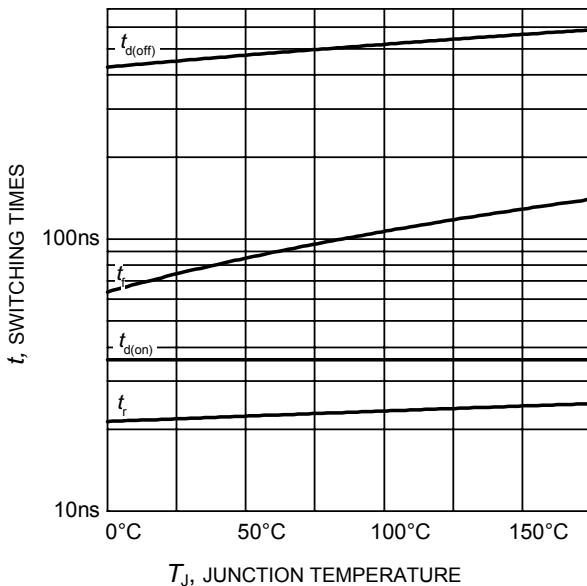


Figure 11. Typical switching times as a function of junction temperature
 (inductive load, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=8\text{A}$,
 $R_G=81\Omega$,
 Dynamic test circuit in Figure E)

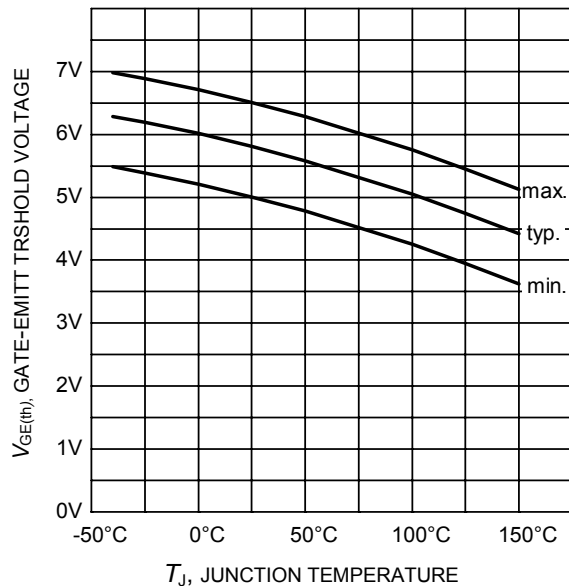


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
 ($I_C = 0.3\text{mA}$)

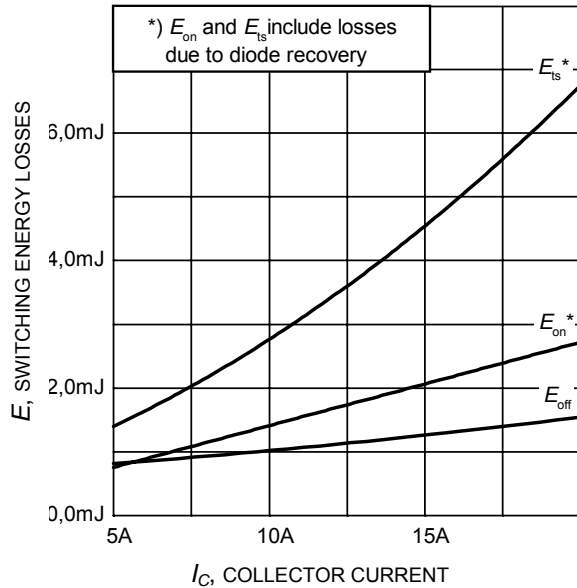


Figure 13. Typical switching energy losses as a function of collector current
 (inductive load, $T_J=150^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=81\Omega$,
 Dynamic test circuit in Figure E)

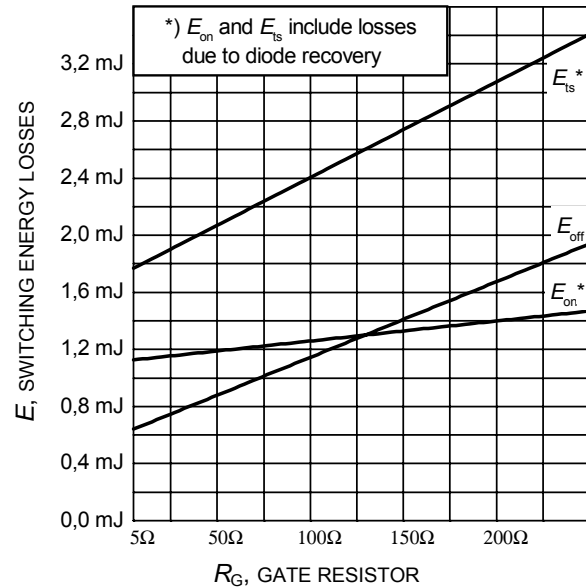


Figure 14. Typical switching energy losses as a function of gate resistor
 (inductive load, $T_J=150^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=8\text{A}$,
 Dynamic test circuit in Figure E)

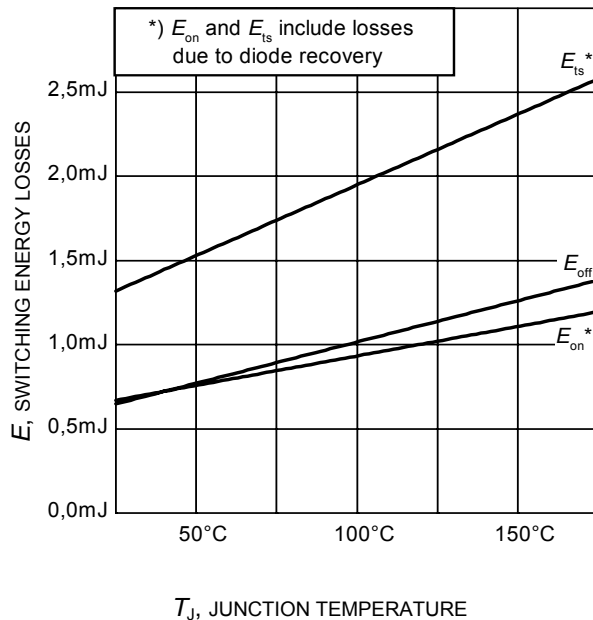


Figure 15. Typical switching energy losses as a function of junction temperature
 (inductive load, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=8\text{A}$,
 $R_G=81\Omega$,
 Dynamic test circuit in Figure E)

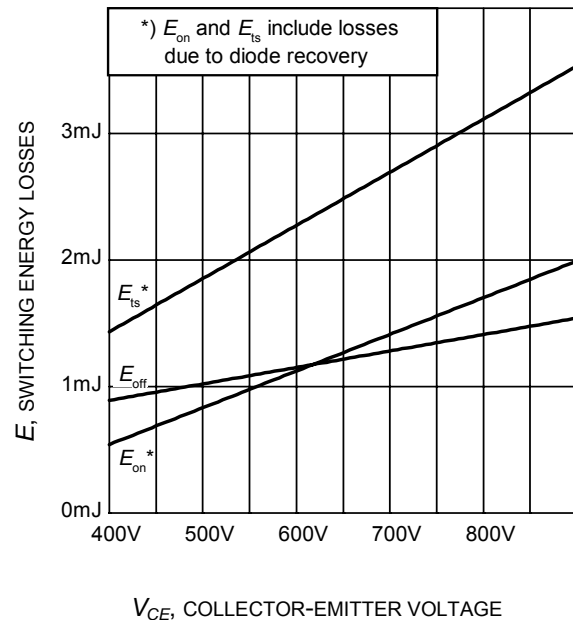


Figure 16. Typical switching energy losses as a function of collector emitter voltage
 (inductive load, $T_J=150^\circ\text{C}$, $V_{GE}=0/15\text{V}$, $I_C=8\text{A}$,
 $R_G=81\Omega$,
 Dynamic test circuit in Figure E)

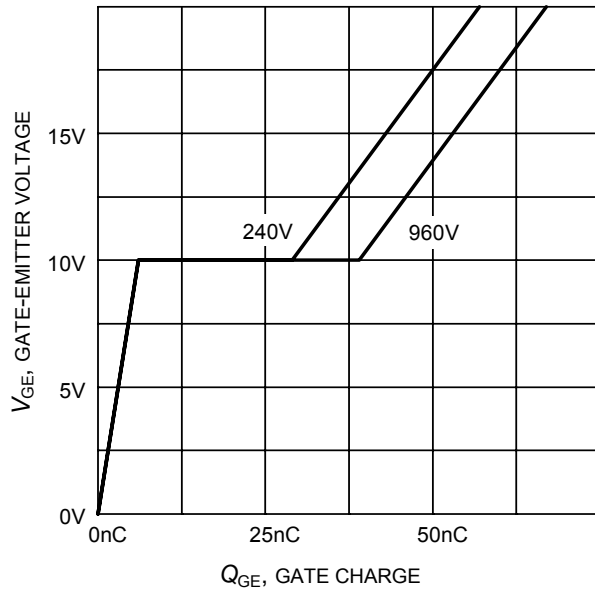


Figure 17. Typical gate charge
($I_C=8\text{ A}$)

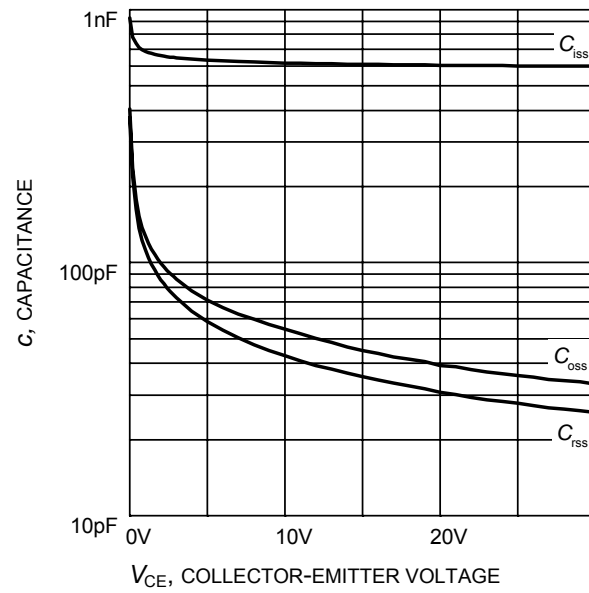


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0\text{V}$, $f = 1\text{ MHz}$)

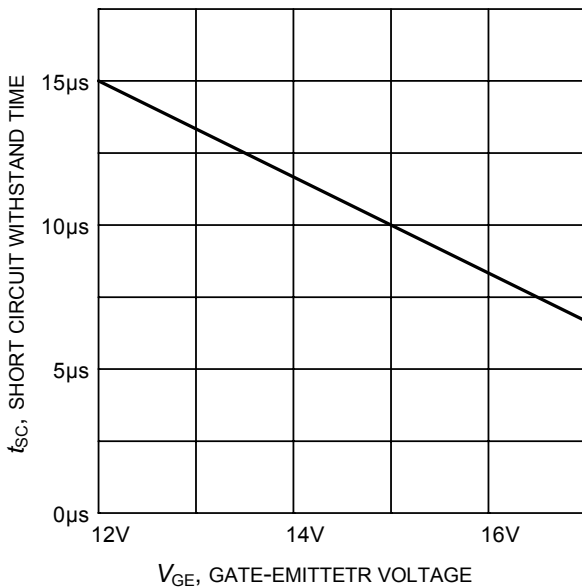


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE}=600\text{V}$, start at $T_J=25^\circ\text{C}$)

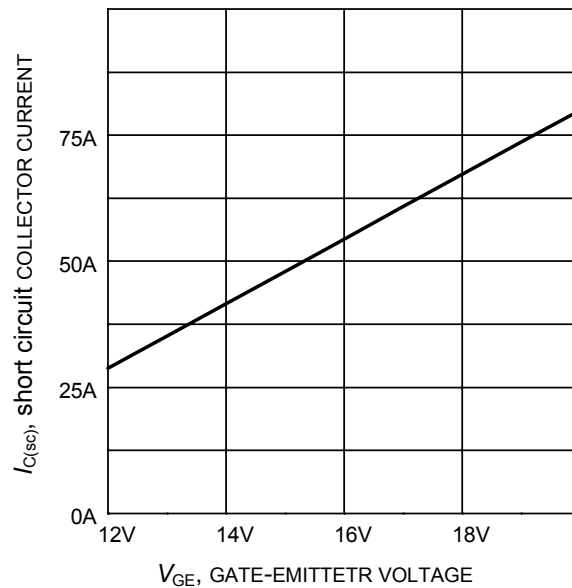


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 600\text{V}$, $T_J \leq 150^\circ\text{C}$)

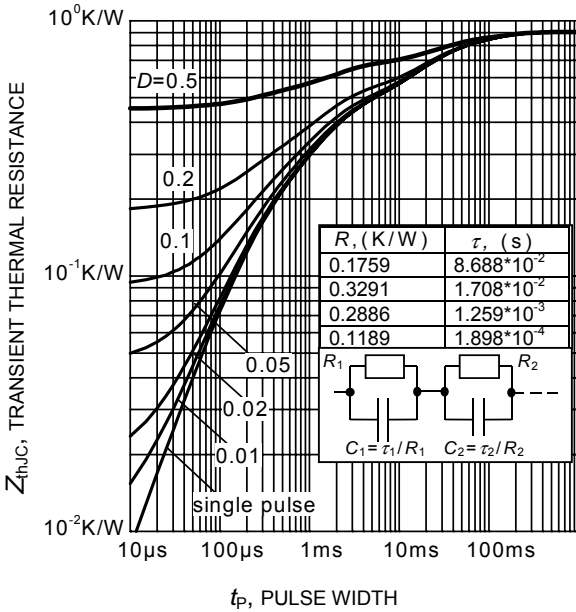


Figure 23. IGBT transient thermal resistance as a function of pulse width
($D = t_p / T$)

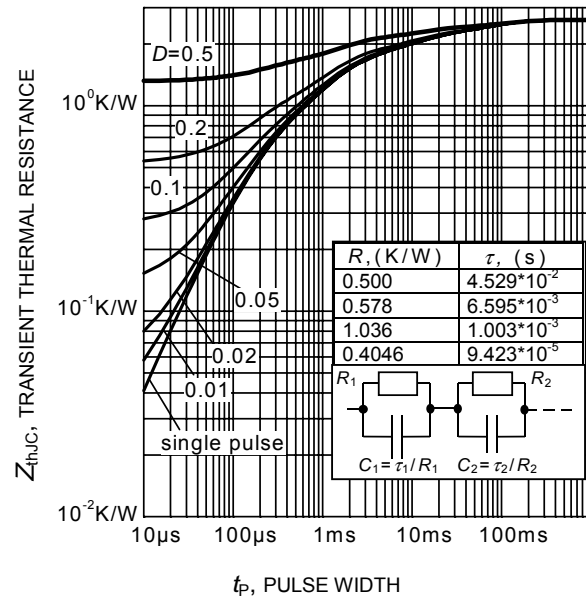


Figure 24. Diode transient thermal impedance as a function of pulse width
($D = t_p / T$)

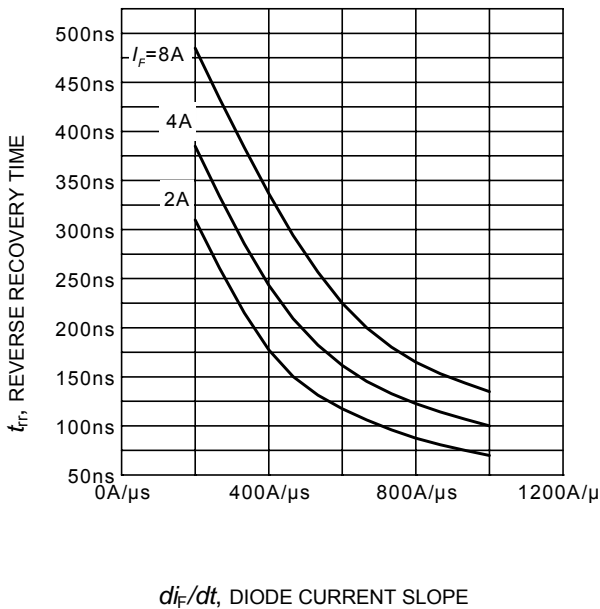


Figure 23. Typical reverse recovery time as a function of diode current slope
($V_R = 600V$, $I_F = 8A$,
Dynamic test circuit in Figure E)

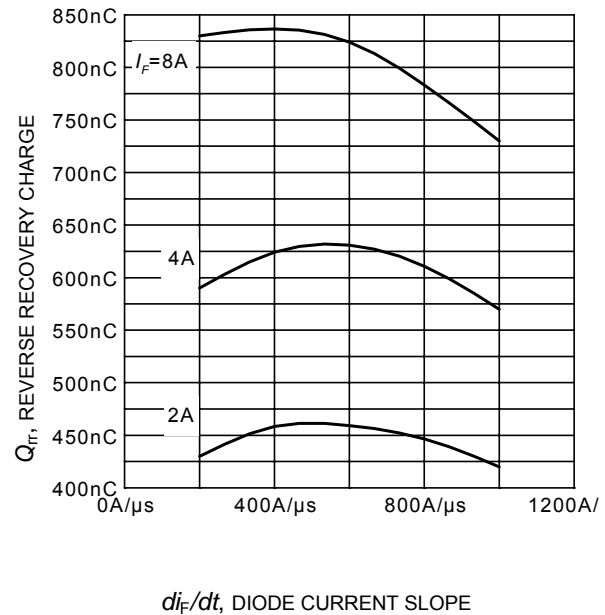
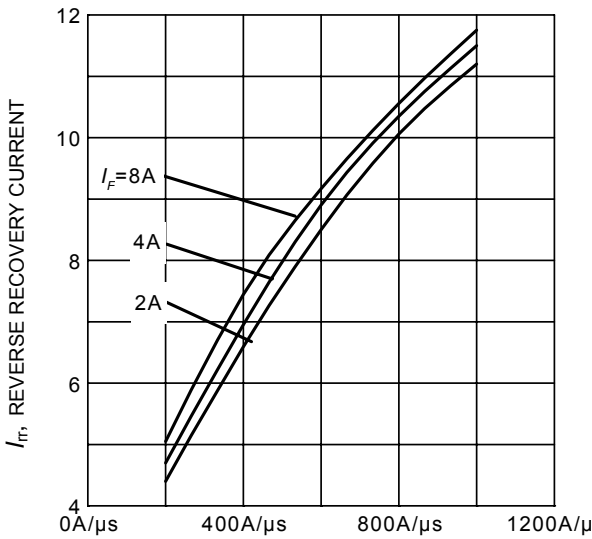
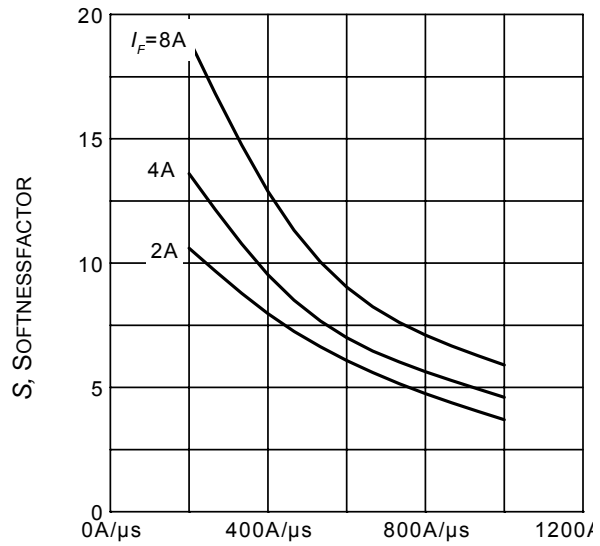


Figure 24. Typical reverse recovery charge as a function of diode current slope
($V_R = 800V$, $T_J = 125^\circ C$,
Dynamic test circuit in Figure E)



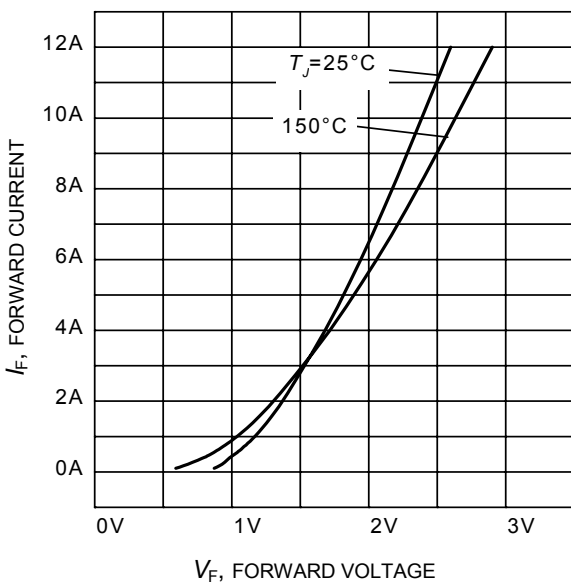
di_F/dt , DIODE CURRENT SLOPE

Figure 25. Typical reverse recovery current as a function of diode current slope
 ($V_R=800V$, $T_J = 125^\circ C$,
 Dynamic test circuit in Figure E)



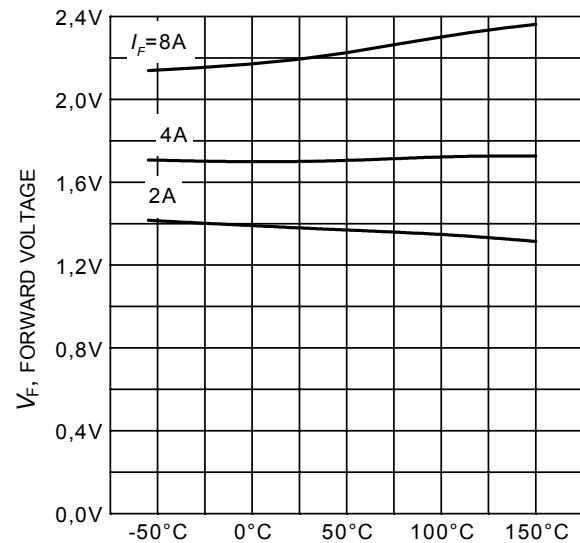
di_F/dt , DIODE CURRENT SLOPE

Figure 26. Typical reverse recovery softness factor as a function of diode current slope
 ($V_R=800V$, $T_J = 125^\circ C$,
 Dynamic test circuit in Figure E)



V_F , FORWARD VOLTAGE

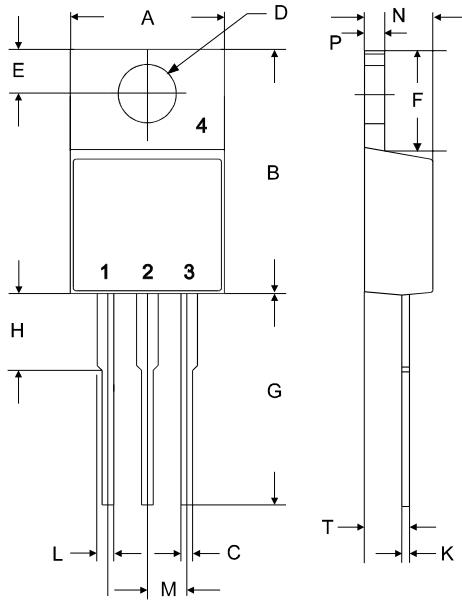
Figure 27. Typical diode forward current as a function of forward voltage



T_J , JUNCTION TEMPERATURE

Figure 28. Typical diode forward voltage as a function of junction temperature

TO-220AB



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071

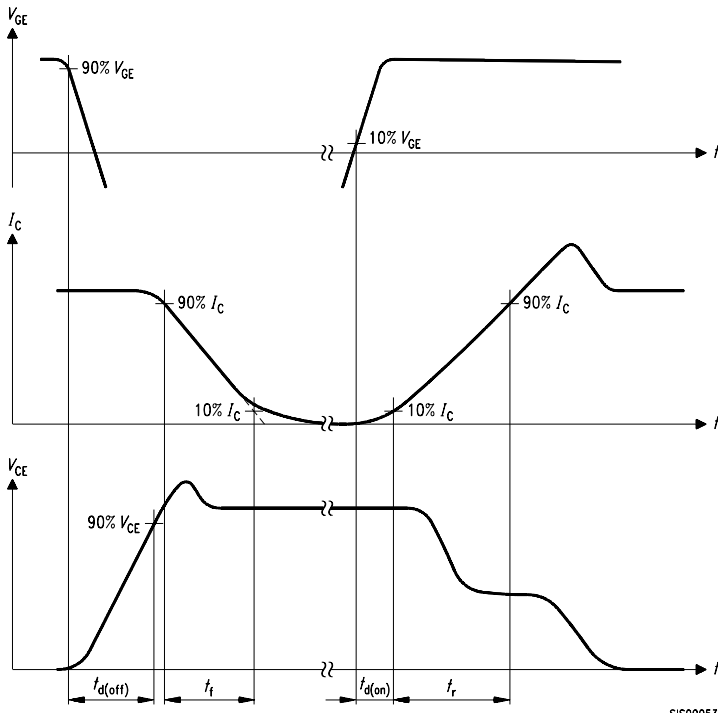


Figure A. Definition of switching times

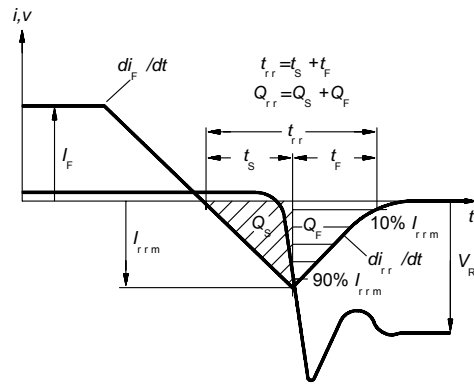


Figure C. Definition of diodes switching characteristics

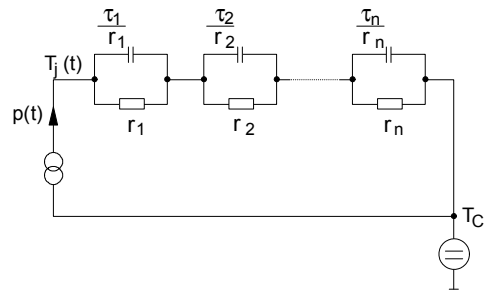


Figure D. Thermal equivalent circuit

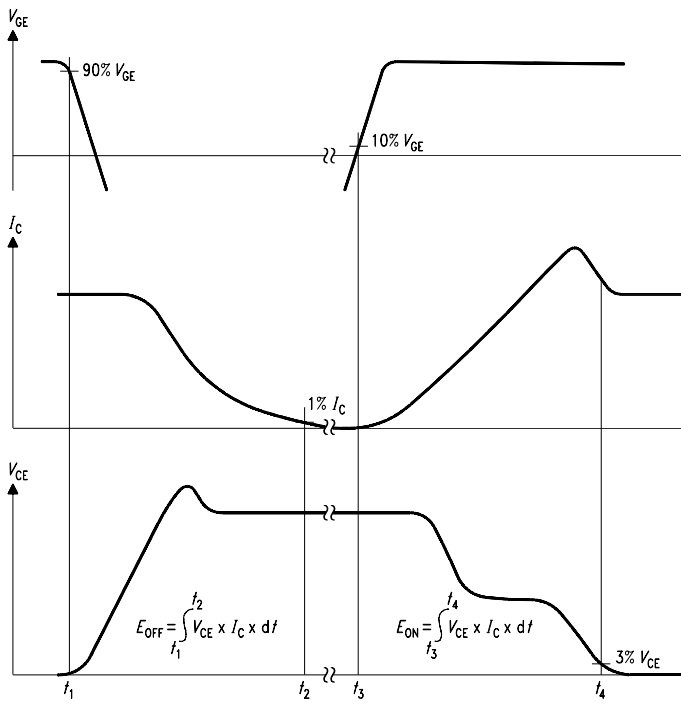


Figure B. Definition of switching losses

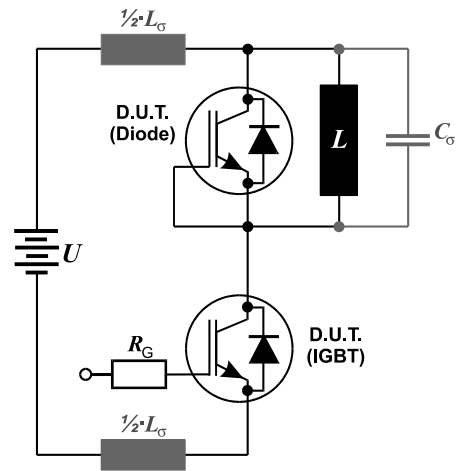


Figure E. Dynamic test circuit
Leakage inductance $L_\sigma = 180\text{nH}$
and Stray capacity $C_\sigma = 39\text{pF}$.

Published by
Infineon Technologies AG,
Bereich Kommunikation
St.-Martin-Strasse 53,
D-81541 München
© Infineon Technologies AG 2001
All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.